

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

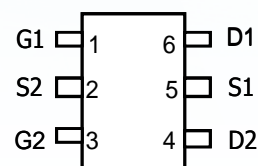
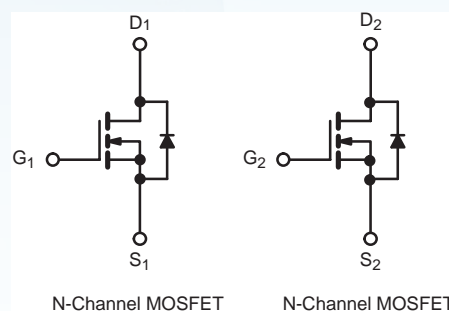
▶ Domestic	Part Number	AO6800
▶ Overseas	Part Number	AO6800
▶ Equivalent	Part Number	AO6800

EV is the abbreviation of name EVVO

Dual N-Channel MOSFET

PRODUCT SUMMARY

- $V_{DS} (V) = 20V$
- $R_{DS(ON)} < 30m\Omega$ ($V_{GS} = 10 V$)
- $R_{DS(ON)} < 43 m\Omega$ ($V_{GS} = 4.5V$)



SOT23-6

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150\text{ }^\circ\text{C}$)	I_D	$T_C = 25\text{ }^\circ\text{C}$	6.0
		$T_C = 70\text{ }^\circ\text{C}$	4.0
		$T_A = 25\text{ }^\circ\text{C}$	3.5 ^{b, c}
		$T_A = 70\text{ }^\circ\text{C}$	2.8 ^{b, c}
Pulsed Drain Current	I_{DM}	18	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	1.17
		$T_A = 25\text{ }^\circ\text{C}$	0.95 ^{b, c}
Maximum Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	1.6
		$T_C = 70\text{ }^\circ\text{C}$	1.0
		$T_A = 25\text{ }^\circ\text{C}$	1.14 ^{b, c}
		$T_A = 70\text{ }^\circ\text{C}$	0.73 ^{b, c}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	93	110	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Foot	R_{thJF}	75	90	

Notes:

- $T_C = 25\text{ }^\circ\text{C}$.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5\text{ s}$.
- Maximum under steady state conditions is 150 $^\circ\text{C}/\text{W}$.

Dual N-Channel MOSFET

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted

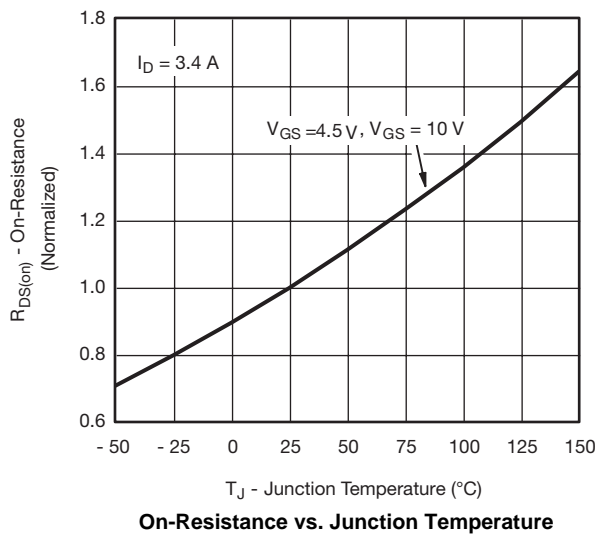
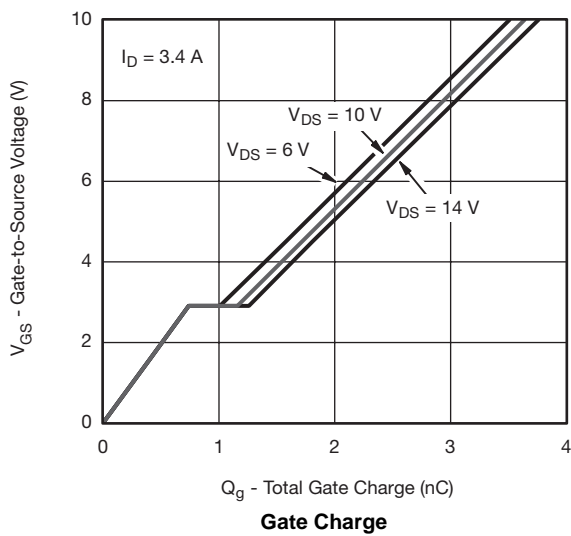
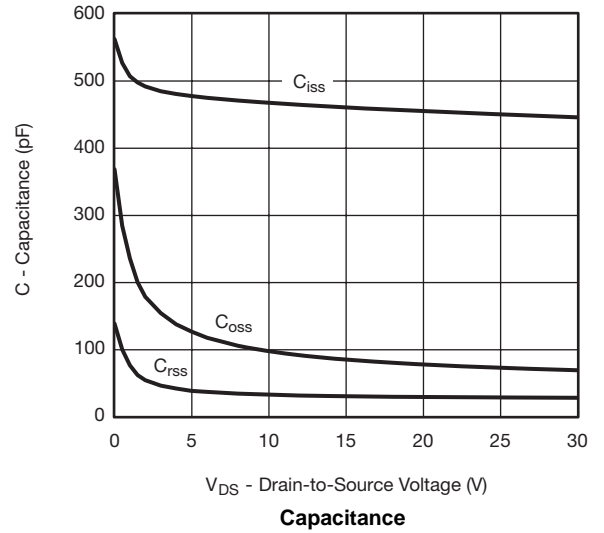
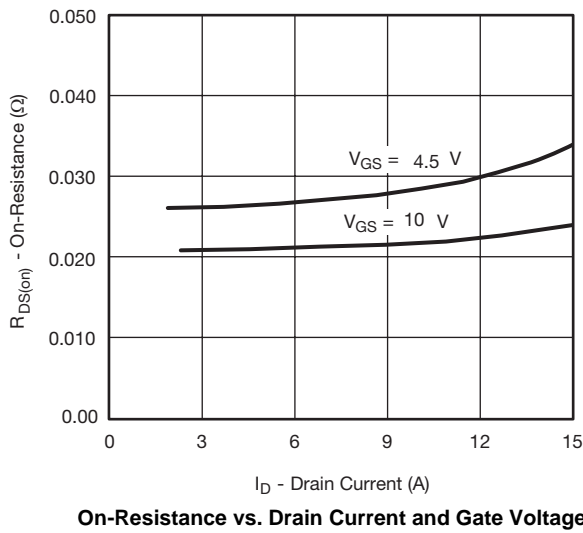
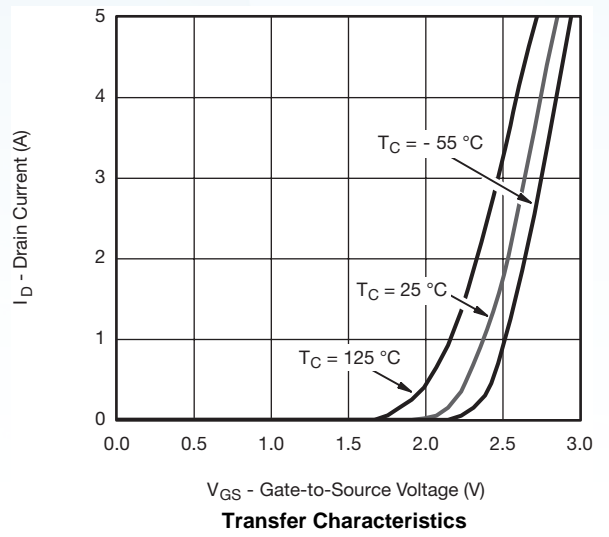
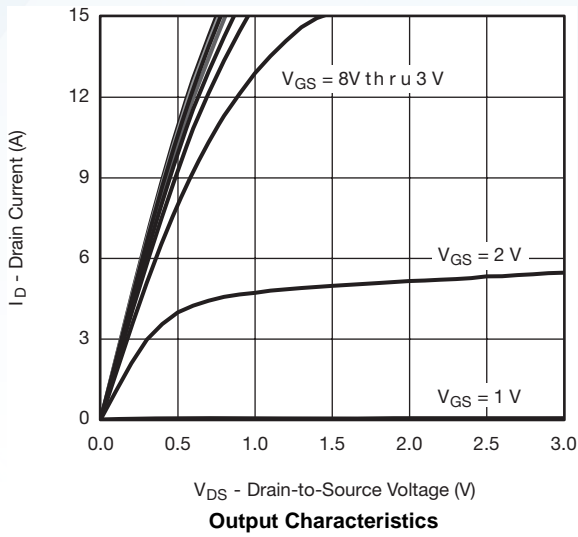
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		29		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.4		1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.4\text{ A}$		30		m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 3.0\text{ A}$		43		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 3.4\text{ A}$		10		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		400		pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{riss}			26		
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 3.4\text{ A}$		3.7	6	nC
				1.8	3	
Gate-Source Charge	Q_{gs}	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 3.4\text{ A}$		0.74		nC
Gate-Drain Charge	Q_{gd}			0.42		
Gate Resistance	R_g		$f = 1\text{ MHz}$	1	5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 5.6\text{ }\Omega$ $I_D \cong 2.7\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		10	20	ns
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 5.6\text{ }\Omega$ $I_D \cong 2.7\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		5	10	
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$		1.2		A
Pulse Diode Forward Current	I_{SM}			18		
Body Diode Voltage	V_{SD}	$I_S = 2.7\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 2.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		10	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}			4	10	nC
Reverse Recovery Fall Time	t_a			6		ns
Reverse Recovery Rise Time	t_b			4		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.

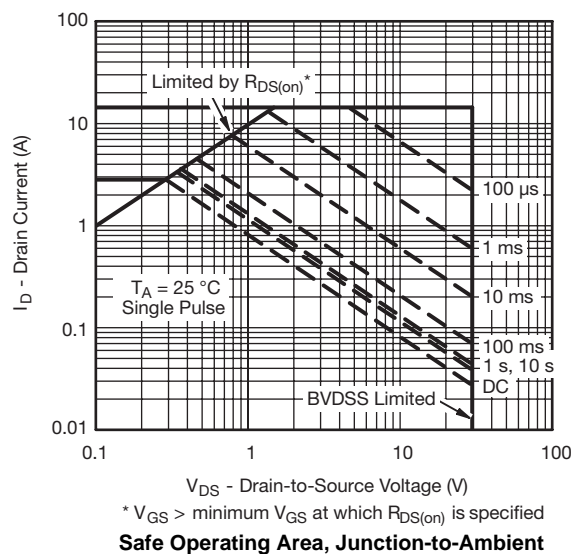
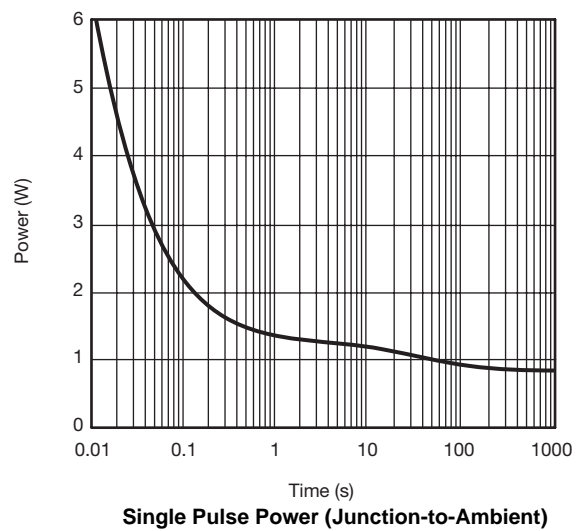
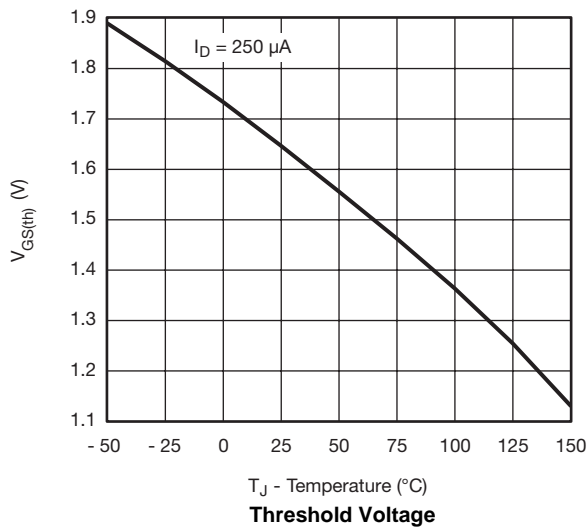
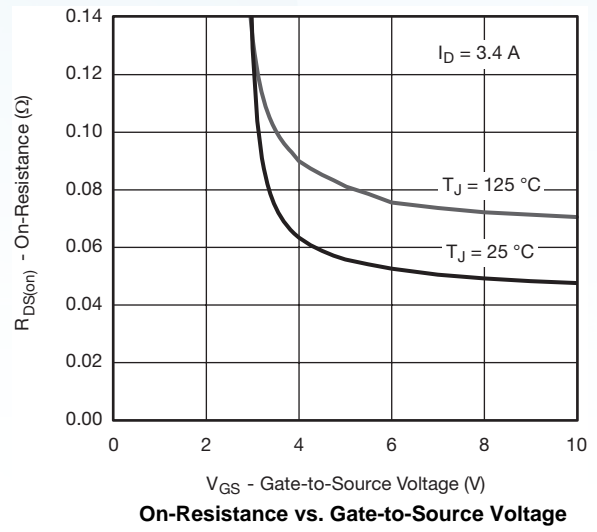
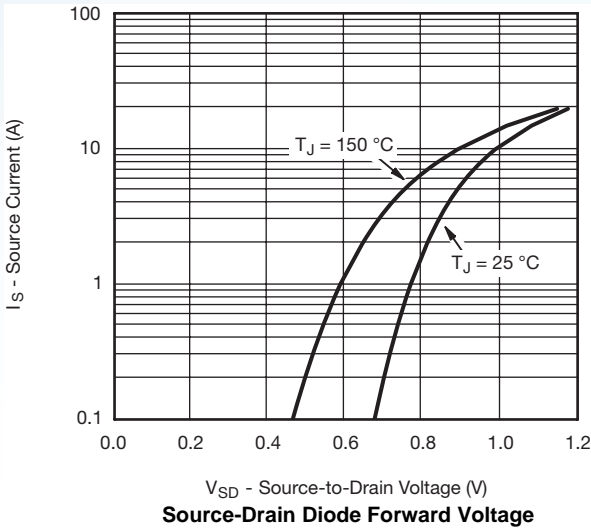
Dual N-Channel MOSFET

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



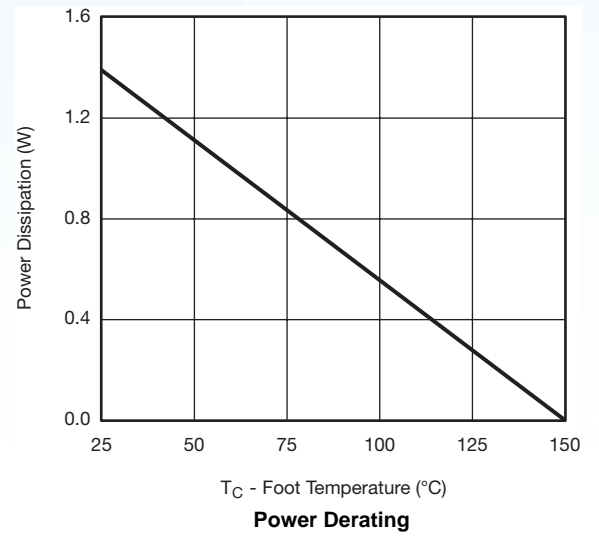
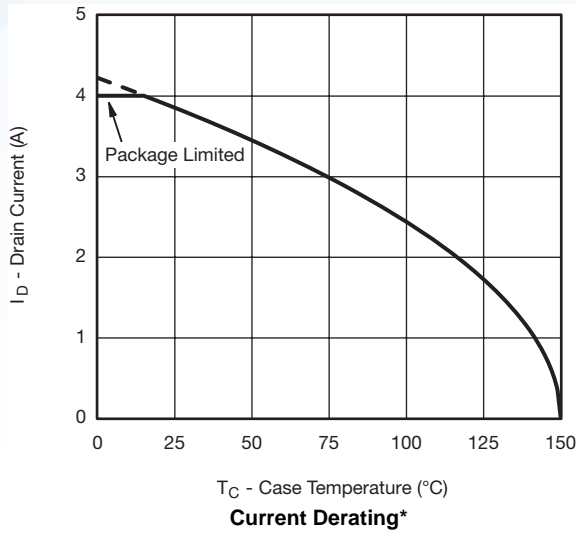
Dual N-Channel MOSFET

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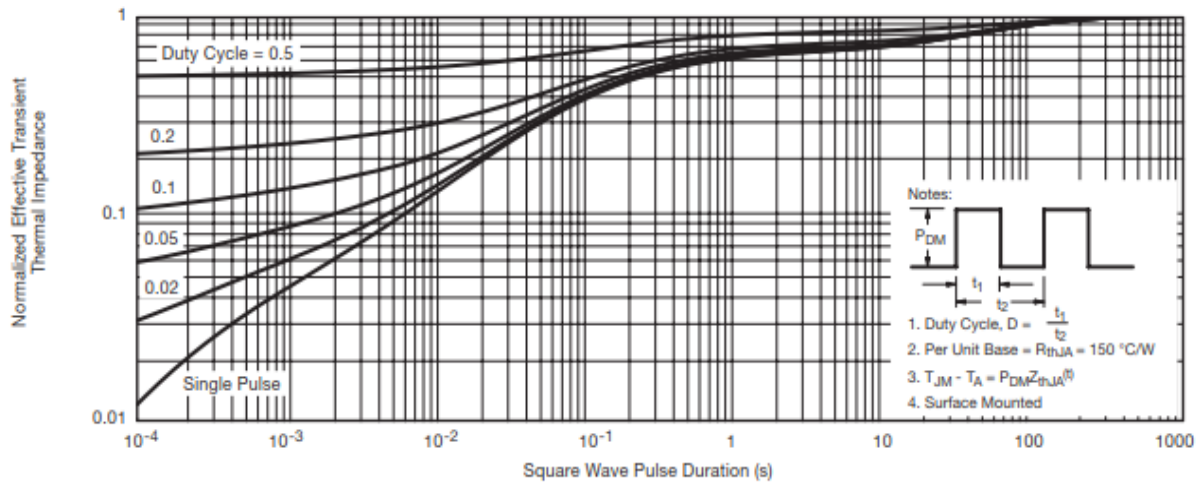
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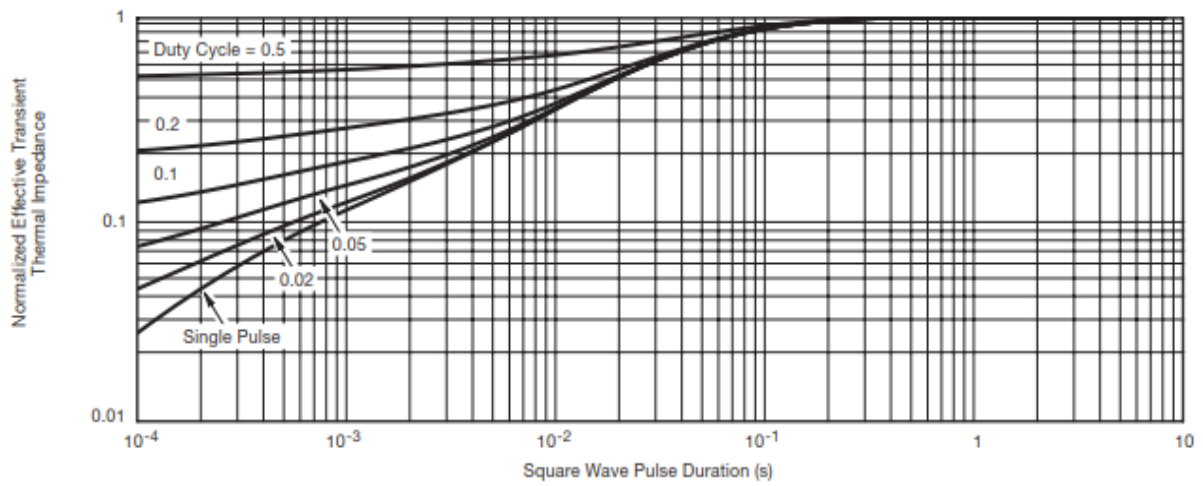
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Dual N-Channel MOSFET

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

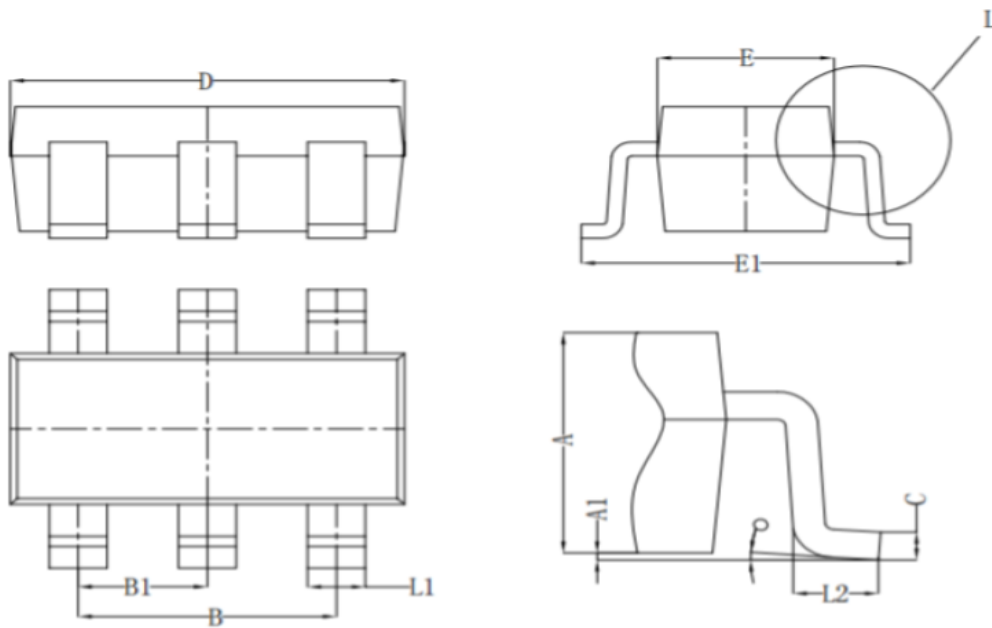


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SOT23- 6 PACKAGE OUTLIE DIMENSIONS

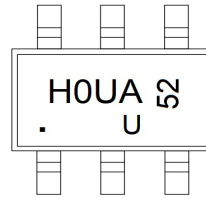


Detail L

Symbol	Dim in mm		
	Min	Nor	Max
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP		
L2	0.300	0.450	0.600
o	0°	4°	8°

Marking

Dual N-Channel MOSFET



Ordering information

Order code	Package	Baseqty	Deliverymode
AO6800	SOT23-6	3000	Tape and reel

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